## Evolution of structure and local atomic environment upon pressure-induced metallization in intermetallic FeGa<sub>3</sub>

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Keywords: Narrow bandgap systems, x-ray absorption spectroscopy, x-ray diffraction, high pressure, disordered alloys,.

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External pressure is applied to the hybridizationgapped semiconductor FeGa<sub>3</sub> to modify the Fe-3d/Ga-4p hybridization strength. This permits tuning its physical without introducing chemical properties any Pressure is thus a preferred tool for perturbation. such perturbing narrow band-gap intermetallic compounds and probing the response. This is primarily to tune the system to charge-gap closure, particularly from the effect of varying electron correlation strength, U/W, where U is the on-site repulsion and W the bandwidth.

Theoretical calculations of intermetallic  $FeGa_3$ estimated the U/W ratio to be 0.6 with U about 3-4 eV [1], thus rendering the system as having moderate electron correlations. The calculations also indicate gapclosure occurs at 25 GPa, due to a strong rearrangement of Fe 3d and Ga 4p hybridization near the Fermi level.

Investigations of the lattice structure as a function of pressure in  $FeGa_3$  is a first step in the comparison between calculations and experiments, which also helps to contrain free parameter values involved in the computational studies. The critical pressure to attain metallization is readily established from electrical-transport measurements.

To understand the effect of varying hybridization and electron correlations in FeGa<sub>3</sub>, we have undertaken both x-ray powder diffraction (HP-XRPD) and variable temperature electrical resistivity measurements to high pressures [2]. These results were complimented by high pressure x-ray absorption spectroscopy (XAS) measurements [2] to provide site-specific local structural information.

Our HP-XRPD results evidence initiation of a structural phase transition in FeGa3 above 16 GPa, with a broad coexistence range involving the low pressure tetragonal phase and the nascent high pressure phase up to 30-35 GPa. Onset of metallic behavior occurs just beyond ~16 GPa, close to the critical pressure where the new high pressure phase starts to emerge. There is a square-root temperature dependence of the resisitivity below the resistivity minimum at ~10 K for data in the metallic state above 16 GPa. This is typical of disordered metallic alloys with enhanced electron-electron interactions. Ga K-edge XAS evidences significant atomic arrangements above 19 GPa indicative of differing Ga local environments of low and high pressure phases of FeGa<sub>3</sub>.



*Figure 1*. HP-XRPD data evidencing the evolution of the lowpressure (LP) phase to a new high pressure (HP) phase initiated at 16-18 GPa.

The interplay between structural aspects of the phase transition and "bad" metallic behavior subsequent to gapclosure from pressurization of the FeGa<sub>3</sub> intermetallic, will be discussed in further detail.

Acknowledgments: Research funding for this project from the URC of the University of Johannesburg is also acknowledged with gratitude. G.R.H., E.C., and S.B. acknowledge financial support from the NRF of South Africa (Grants No. 105870 and No. 90698, and for a postdoctoral research fellowship award). B.J. acknowledges IISc Bangalore and ICTP Trieste for financial support through the award of the IISc-ICTP fellowship. We also thank various beamline scientists at the ID-24 of the ESRF for assistance with the XAS measurements.

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